Binary/Decade Up/Down Counter

The MC14029B Binary/Decade up/down counter is constructed with MOS P-channel and N-channel enhancement mode devices in a single monolithic structure. The counter consists of type D flip-flop stages with a gating structure to provide toggle flip-flop capability. The counter can be used in either Binary or BCD operation. This complementary MOS counter finds primary use in up/down and difference counting and frequency synthesizer applications where low power dissipation and/or high noise immunity is desired. It is also useful in A/D and D/A conversion and for magnitude and sign generation.

Features

- Diode Protection on All Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Internally Synchronous for High Speed
- Logic Edge-Clocked Design Count Occurs on Positive Going Edge of Clock
- Asynchronous Preset Enable Operation
- Capable of Driving Two Low-Power TTL Loads or One Low-Power Schottky TTL Load Over the Rated Temperature Range
- Pin for Pin Replacement for CD4029B
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- This Device is Pb–Free and is RoHS Compliant



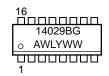
ON Semiconductor®

www.onsemi.com



SOIC-16 D SUFFIX CASE 751B

MARKING DIAGRAM



A = Assembly Location

 $\begin{array}{ll} \text{WL} &= \text{Wafer Lot} \\ \text{YY, Y} &= \text{Year} \\ \text{WW} &= \text{Work Week} \\ \text{G} &= \text{Pb-Free Indicator} \end{array}$

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	-0.5 to +18.0	V
V _{in} , V _{out}	Input or Output Voltage Range (DC or Transient)	–0.5 to V _{DD} + 0.5	V
I _{in} , I _{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P _D	Power Dissipation, per Package (Note 1)	500	mW
T _A	Ambient Temperature Range	-55 to +125	°C
T _{stg}	Storage Temperature Range	-65 to +150	°C
T_L	Lead Temperature (8–Second Soldering)	260	°C

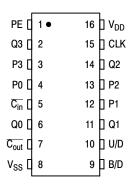
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in} \text{ or } V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

^{1.} Temperature Derating: "D/DW" Packages: -7.0 mW/°C From 65°C To 125°C

PIN ASSIGNMENT



TRUTH TABLE

Carry In	Up/Down	Preset Enable	Action
1	X	0	No Count
0	1	0	Count Up
0	0	0	Count Down
Х	X	1	Preset

X = Don't Care

ORDERING INFORMATION

Device	Package	Shipping [†]
MC14029BDR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
NLV14029BDR2G*	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging

Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

				-5	5°C	25°C			12	5°C	
Characteristic		Symbol	V _{DD} Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage	"0" Level	V_{OL}	5.0	_	0.05	_	0	0.05	_	0.05	Vdc
$V_{in} = V_{DD}$ or 0			10	_	0.05	_	0	0.05	_	0.05	
			15	_	0.05	_	0	0.05	_	0.05	
	"1" Level	V _{OH}	5.0	4.95	_	4.95	5.0	_	4.95	-	Vdc
$V_{in} = 0 \text{ or } V_{DD}$	1 LOVOI	0	10	9.95	_	9.95	10	_	9.95	_	
Vin = 0 Oi VDD			15	14.95	_	14.95	15	_	14.95	_	
Input Voltage	"0" Level	V _{IL}									Vdc
$(V_O = 4.5 \text{ or } 0.5 \text{ Vdc})$			5.0	_	1.5	_	2.25	1.5	_	1.5	
$(V_O = 9.0 \text{ or } 1.0 \text{ Vdc})$			10	_	3.0	_	4.50	3.0	_	3.0	
$(V_O = 13.5 \text{ or } 1.5 \text{ Vdc})$			15	_	4.0	_	6.75	4.0	_	4.0	
	"1" Level	V _{IH}									Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$			5.0	3.5	_	3.5	2.75	_	3.5	_	
$(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$			10	7.0	_	7.0	5.50	_	7.0	_	
$(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$			15	11	_	11	8.25	_	11	_	
Output Drive Current		I _{OH}									mAdc
(V _{OH} = 2.5 Vdc)	Source	011	5.0	-3.0	_	-2.4	-4.2	_	-1.7	_	
$(V_{OH} = 4.6 \text{ Vdc})$			5.0	-0.64	_	-0.51	-0.88	_	-0.36	_	
$(V_{OH} = 9.5 \text{ Vdc})$			10	-1.6	_	-1.3	-2.25	_	-0.9	_	
$(V_{OH} = 13.5 \text{ Vdc})$			15	-4.2	_	-3.4	-8.8	-	-2.4	_	
(V _{OL} = 0.4 Vdc)	Sink	I _{OL}	5.0	0.64	_	0.51	0.88	_	0.36	_	mAdc
$(V_{OL} = 0.5 \text{ Vdc})$			10	1.6	_	1.3	2.25	_	0.9	_	
$(V_{OL} = 1.5 \text{ Vdc})$			15	4.2	_	3.4	8.8	_	2.4	_	
Input Current		I _{in}	15	_	±0.1	-	±0.00001	±0.1	-	±1.0	μAdc
Input Capacitance, (V _{in} = 0)		C _{in}	-	_	-	-	5.0	7.5	-	_	pF
Quiescent Current		I _{DD}	5.0	_	5.0	_	0.005	5.0	_	150	μAdc
(Per Package)			10	_	10	_	0.010	10	_	300	
			15	_	20	_	0.015	20	_	600	
Total Supply Current (Notes 3	& 4)	Ι _Τ	5.0		•	I _T = (0	.58 μA/kHz)	f + I _{DD}	•	•	μAdc
(Dynamic plus Quiescent, Per Package)			10			$I_{T} = (1$.20 μA/kHz)	f + I _{DD}			
(C _L = 50 pF on all outputs, a switching)	all buffers		15			I _T = (1	.70 μA/kHz)	f + I _{DD}			

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

3. The formulas given are for the typical characteristics only at 25°C.

4. To calculate total supply current at loads other than 50 pF:

I_T(C_L) = I_T(50 pF) + (C_L – 50) Vfk

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ VfI}$$

where: I_T is in μA (per package), C_L in pF, $V = (V_{DD} - V_{SS})$ in volts, f in kHz is input frequency, and k = 0.001.

SWITCHING CHARACTERISTICS (Note 5) ($C_L = 50 \text{ pF}, T_A = 25^{\circ}C$)

				All Types		
Characteristic	Symbol	V _{DD}	Min	Typ (Note 6)	Max	Unit
Output Rise and Fall Time t_{TLH} , $t_{THL} = (1.5 \text{ ns/pF}) C_L + 25 \text{ ns}$ t_{TLH} , $t_{THL} = (0.75 \text{ ns/pF}) C_L + 12.5 \text{ ns}$ t_{TLH} , $t_{THL} = (0.55 \text{ ns/pF}) C_L + 9.5 \text{ ns}$	t _{TLH} , t _{THL}	5.0 10 15	- - -	100 50 40	200 100 80	ns
Propagation Delay Time Clk to Q $t_{PLH}, t_{PHL} = (1.7 \text{ ns/pF}) C_L + 230 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.66 \text{ ns/pF}) C_L + 97 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.5 \text{ ns/pF}) C_L + 75 \text{ ns}$	t _{PLH} , t _{PHL}	5.0 10 15	- - -	200 100 90	400 200 180	ns
Clk to \overline{C}_{out} t_{PLH} , t_{PHL} = (1.7 ns/pF) C_L + 230 ns t_{PLH} , t_{PHL} = (0.66 ns/pF) C_L + 97 ns t_{PLH} , t_{PHL} = (0.5 ns/pF) C_L + 75 ns	t _{PLH} , t _{PHL}	5.0 10 15	- - -	250 130 85	500 260 190	ns
$\overline{C_{in}}$ to $\overline{C_{out}}$ t_{PLH} , t_{PHL} = (1.7 ns/pF) C_L + 95 ns t_{PLH} , t_{PHL} = (0.66 ns/pF) C_L + 47 ns t_{PLH} , t_{PHL} = (0.5 ns/pF) C_L + 35 ns	t _{PLH} , t _{PHL}	5.0 10 15	- - -	175 50 50	360 120 100	ns
PE to Q t_{PLH} , t_{PHL} = (1.7 ns/pF) C_L + 230 ns t_{PLH} , t_{PHL} = (0.66 ns/pF) C_L + 97 ns t_{PLH} , t_{PHL} = (0.5 ns/pF) C_L + 75 ns	t _{PLH} , t _{PHL}	5.0 10 15	- - -	235 100 80	470 200 160	ns
PE to $\overline{C_{out}}$ t_{PLH} , $t_{PHL} = (1.7 \text{ ns/pF}) C_L + 465 \text{ ns}$ t_{PLH} , $t_{PHL} = (0.66 \text{ ns/pF}) C_L + 192 \text{ ns}$ t_{PLH} , $t_{PHL} = (0.5 \text{ ns/pF}) C_L + 125 \text{ ns}$	t _{PLH} , t _{PHL}	5.0 10 15	- - -	320 145 105	640 290 210	ns
Clock Pulse Width	t _{W(cl)}	5.0 10 15	180 80 60	90 40 30	- - -	ns
Clock Pulse Frequency	f _{cl}	5.0 10 15	- - -	4.0 8.0 10	2.0 4.0 5.0	MHz
Preset Removal Time The Preset Signal must be low prior to a positive–going transition of the clock.	t _{rem}	5.0 10 15	160 80 60	80 40 30	- - -	ns
Clock Rise and Fall Time	$\begin{matrix}t_{r(\text{cl})}\\t_{f(\text{cl})}\end{matrix}$	5.0 10 1 5	- - -		15 5 4	μs
Carry In Setup Time	t _{su}	5.0 10 15	150 60 40	75 30 20		ns
Up/Down Setup Time		5.0 10 15	340 140 100	170 70 50	- - -	ns
Binary/Decade Setup Time		5.0 10 15	320 140 100	160 70 50	- - -	ns
Preset Enable Pulse Width	t _W	5.0 10 15	130 70 50	65 35 25	- - -	ns

^{5.} The formulas given are for the typical characteristics only at 25°C.
6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

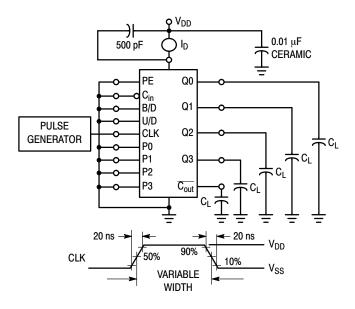


Figure 1. Power Dissipation Test Circuit and Waveform

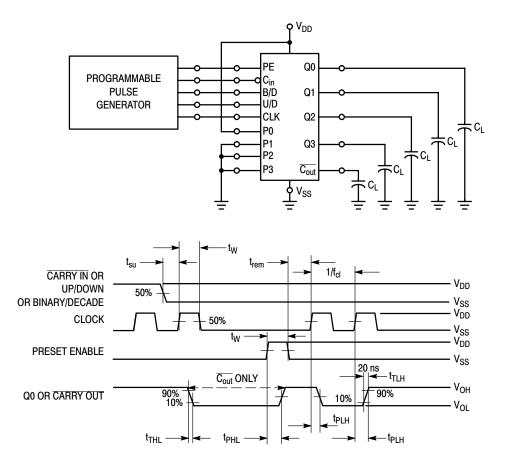
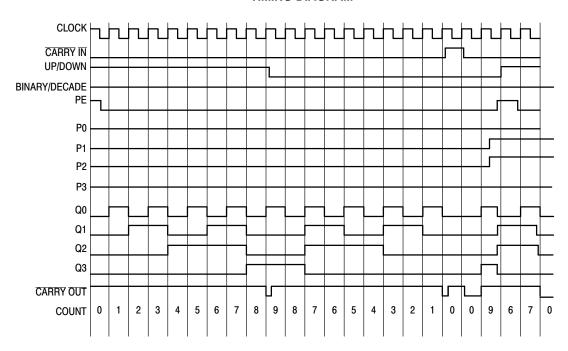
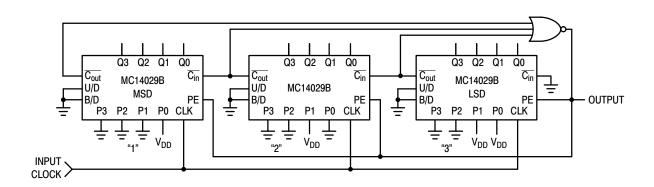


Figure 2. Switching Time Test Circuit and Waveforms

TIMING DIAGRAM





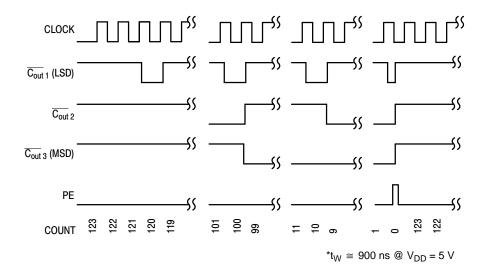
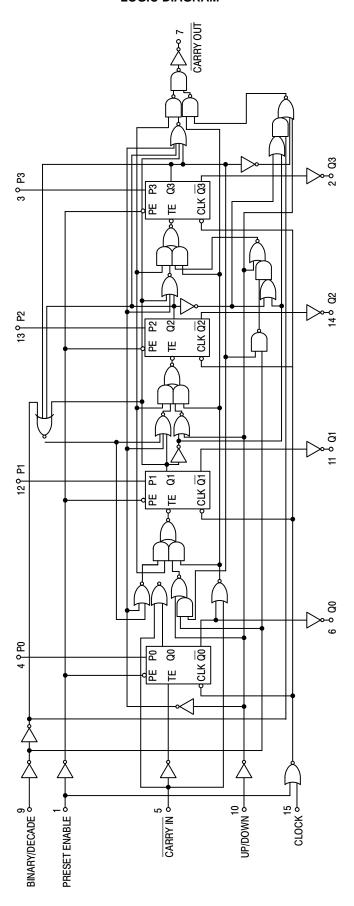


Figure 3. Divide by N BCD Down Counter and Timing Diagram (Shown for N = 123)

LOGIC DIAGRAM



MECHANICAL CASE OUTLINE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050	BSC	
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	#1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE	13.	CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	COL DEDING	FOOTPRINT
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDERING	3 FOOTPRINT
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1		8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1		5.40 →
								7	,.40
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12 <
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPU	T)		. 1	16
3.	DRAIN, #2	3.		3.	COMMON DRAIN (OUTPU			↓ └── ·	" 🗀
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	•,		- —	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPU	T)	16	5X T	
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU		0.5	iii I	· —
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU		0.0		
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU	T)			
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPU	T)			
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPU	T)			
13.	GATE, #2	13.	ANODE	13.	GATE N-CH				
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPU	T)			— V PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPU				<u> </u>
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH				
								8	9 + - + -
								 •	_ - ↑
									DIMENSIONS: MILLIMETERS
									DIMENSIONS: MILLIMETERS

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